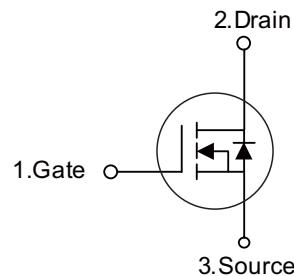


■ PRODUCT CHARACTERISTICS

VDSS	650V
R _{DS(on)} max(@V _{GS} = 10 V)	0.5Ω
Qg@type	54nC
ID	20A

Symbol



■ APPLICATIONS

- High efficiency switch mode power supplies
- Electronic ballasts
- LED power supply

■ FEATURES

- * R_{DS(ON)} ≤ 0.5Ω @ V_{GS}=10V
- * High Switching Speed
- * 100% Avalanche Tested



TO-220



TO-220F

■ ORDER INFORMATION

Order codes		Package	Packing
Halogen-Free	Halogen		
N/A	MOT20N65F	TO-220F	50 pieces/Tube
N/A	MOT20N65A	TO-220	50 pieces/Tube

■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V _{DSS}	650	V
Gate-Source Voltage		V _{GSS}	±30	V
Drain Current	Continuous	I _D	20	A
	Pulsed (Note 2)	I _{DM}	40	A
Avalanche Energy	Single Pulsed (Note 3)	E _{AS}	562	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	2.46	V/ns
Power Dissipation	TO-220	P _D	270	W
	TO-220F		65	W
Junction Temperature		T _J	+150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. L = 10mH, I_{AS} = 10.5A, V_{DD} = 50V, R_G = 25 Ω Starting T_J = 25°C

4. I_{SD} ≤ 20A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

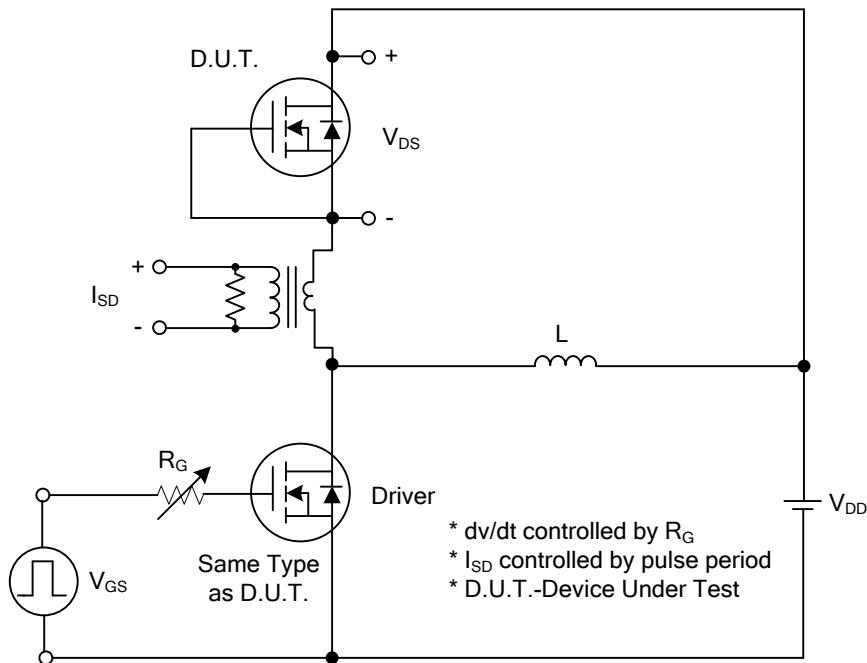
■ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_D=250\mu\text{A}$	650			V
Drain-Source Leakage Current	I_{DSS}	$\text{V}_{\text{DS}}=650\text{V}, \text{V}_{\text{GS}}=0\text{V}$			10	μA
Gate-Source Leakage Current	Forward	$\text{V}_{\text{GS}}=30\text{V}, \text{V}_{\text{DS}}=0\text{V}$			100	nA
	Reverse	$\text{V}_{\text{GS}}=-30\text{V}, \text{V}_{\text{DS}}=0\text{V}$			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$\text{V}_{\text{GS}(\text{TH})}$	$\text{V}_{\text{DS}}=\text{V}_{\text{GS}}, \text{I}_D=250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$\text{R}_{\text{DS}(\text{ON})}$	$\text{V}_{\text{GS}}=10\text{V}, \text{I}_D=10\text{A}$			0.5	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$\text{V}_{\text{GS}}=0\text{V}, \text{V}_{\text{DS}}=25\text{V}, f=1.0\text{MHz}$		2512		pF
Output Capacitance	C_{OSS}			231		pF
Reverse Transfer Capacitance	C_{RSS}			14		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge (Note 1)	Q_G	$\text{V}_{\text{DS}}=100\text{V}, \text{V}_{\text{GS}}=10\text{V}, \text{I}_D=20\text{A}$ $I_G=1\text{mA}$ (Note 1, 2)		54		nC
Gateource Charge	Q_{GS}			10		nC
Gate-Drain Charge	Q_{GD}			13		nC
Turn-on Delay Time (Note 1)	$t_{\text{D}(\text{ON})}$	$\text{V}_{\text{DS}}=100\text{V}, \text{V}_{\text{GS}}=10\text{V}, \text{I}_D=20\text{A},$ $R_G=25\Omega$ (Note 1, 2)		28		ns
Rise Time	t_R			35		ns
Turn-off Delay Time	$t_{\text{D}(\text{OFF})}$			140		ns
Fall-Time	t_F			76		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S				20	A
Maximum Body-Diode Pulsed Current	I_{SM}				40	A
Drain-Source Diode Forward Voltage (Note 1)	V_{SD}	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_S=20\text{A}$			1.4	V
Reverse Recovery Time (Note 1)	t_{rr}	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_S=20\text{A},$ $d\text{I}_F/dt=100\text{A}/\mu\text{s}$ (Note1)		506		ns
Reverse Recovery Charge	Q_{rr}			9		μC

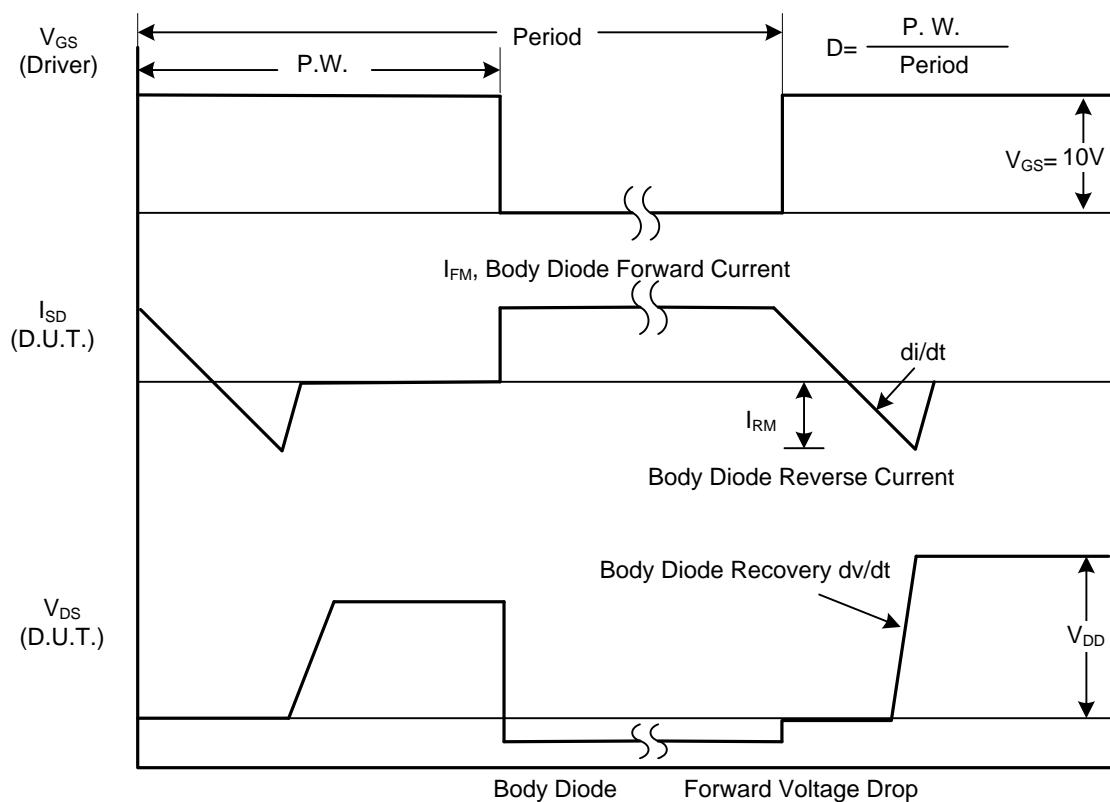
Notes: 1. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

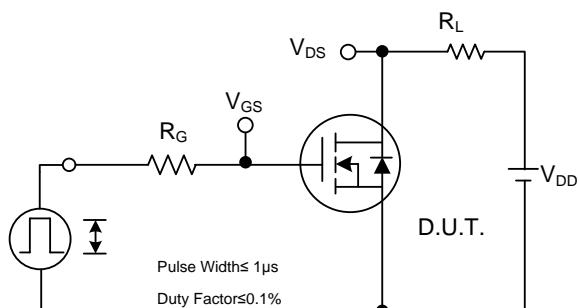


Peak Diode Recovery dv/dt Test Circuit

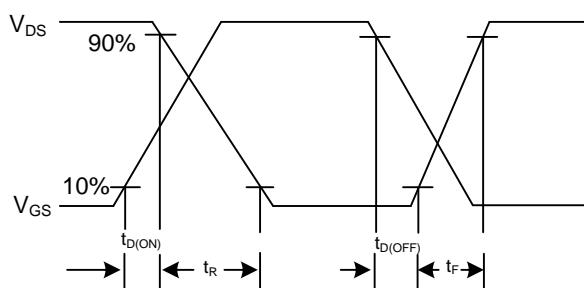


Peak Diode Recovery dv/dt Waveforms

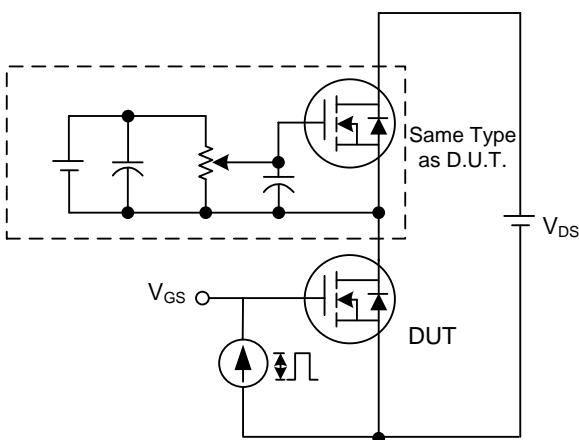
■ TEST CIRCUITS AND WAVEFORMS(Cont.)



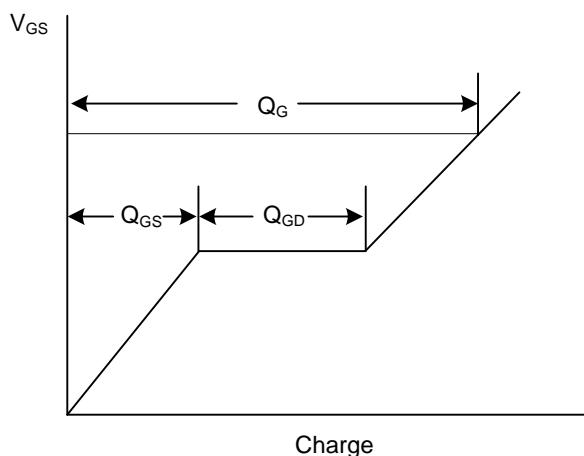
Switching Test Circuit



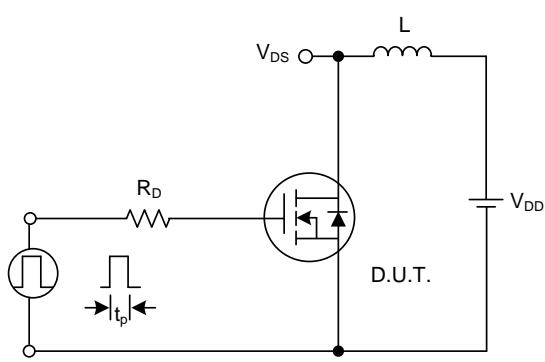
Switching Waveforms



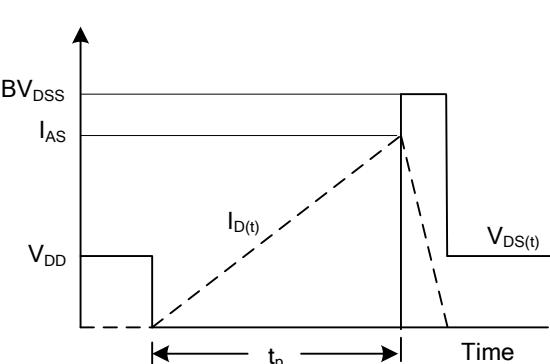
Gate Charge Test Circuit



Gate Charge Waveform

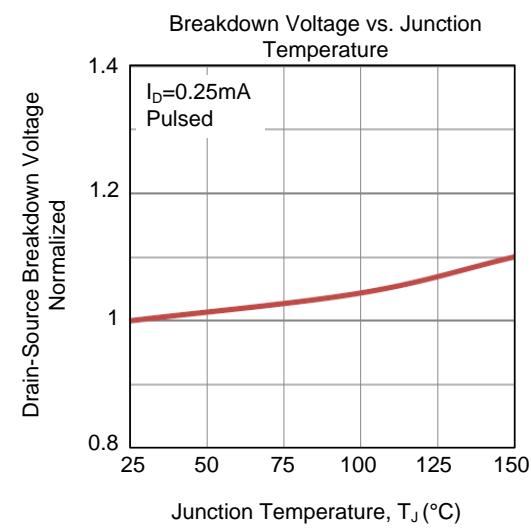
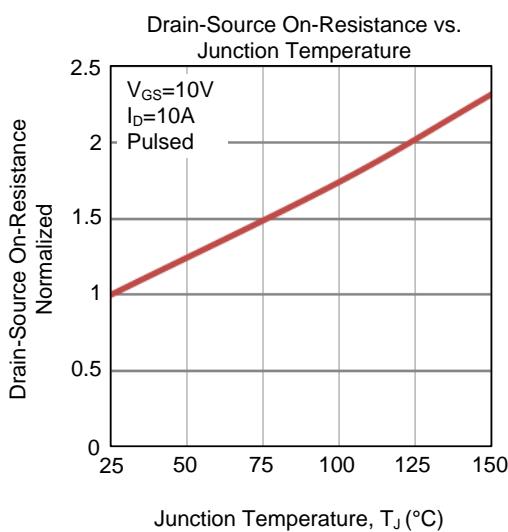
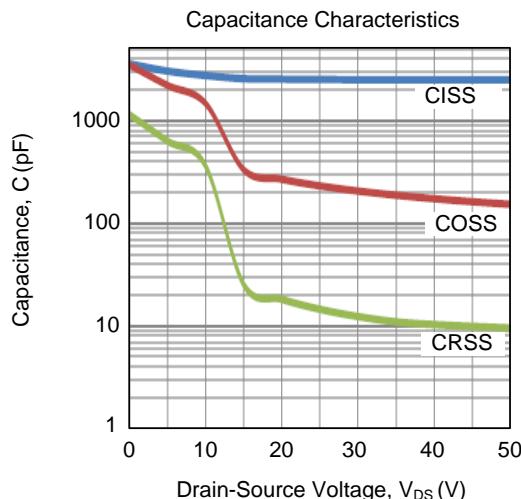
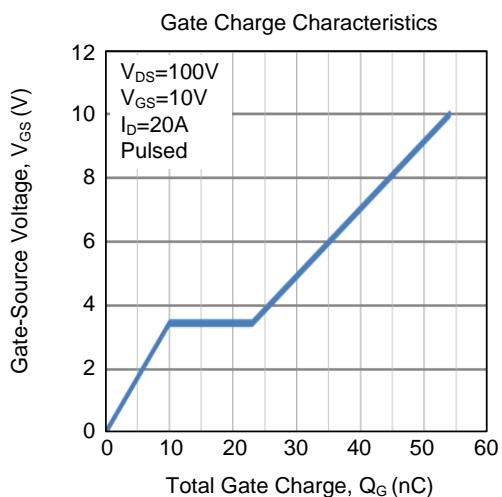
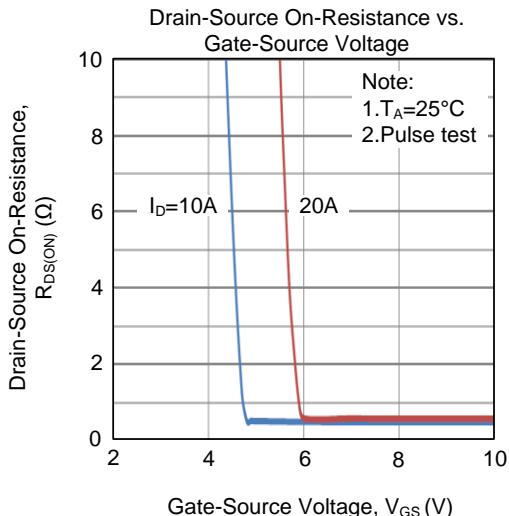
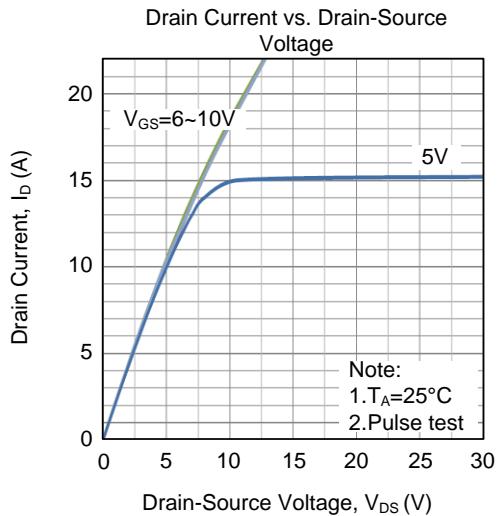


Unclamped Inductive Switching Test Circuit

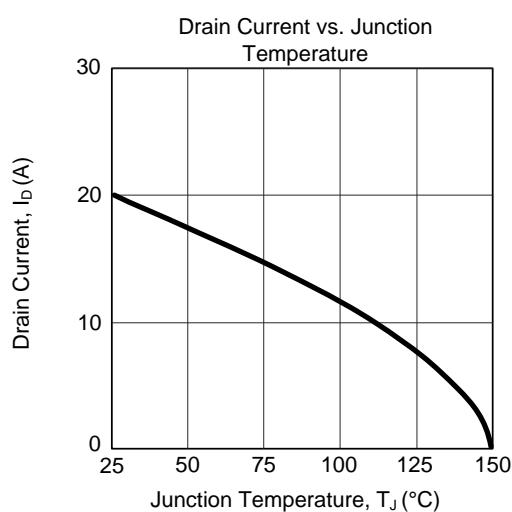
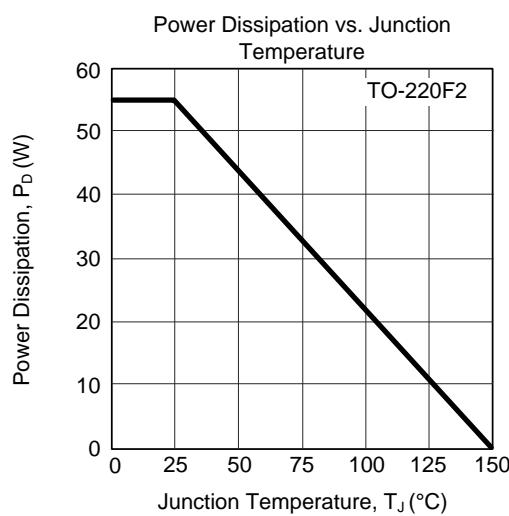
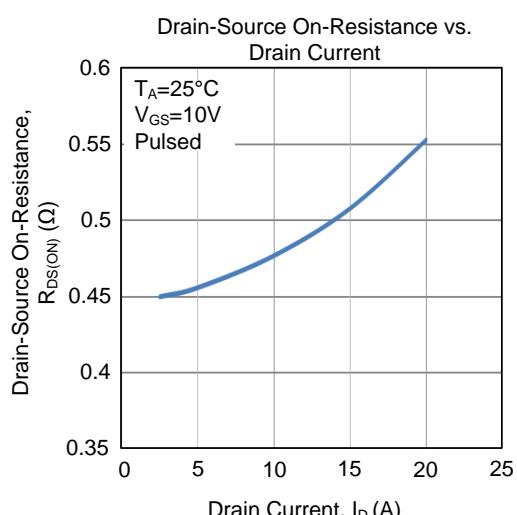
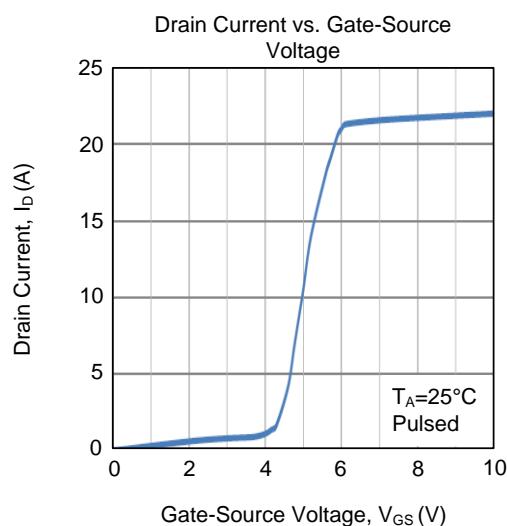
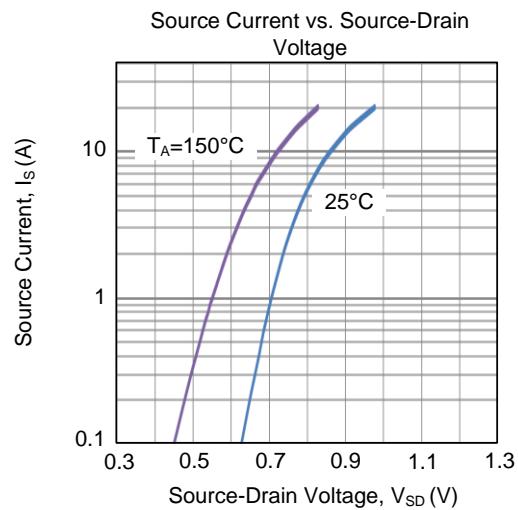
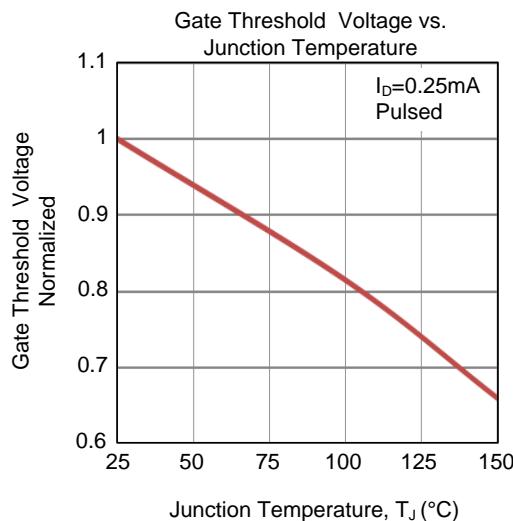


Unclamped Inductive Switching Waveforms

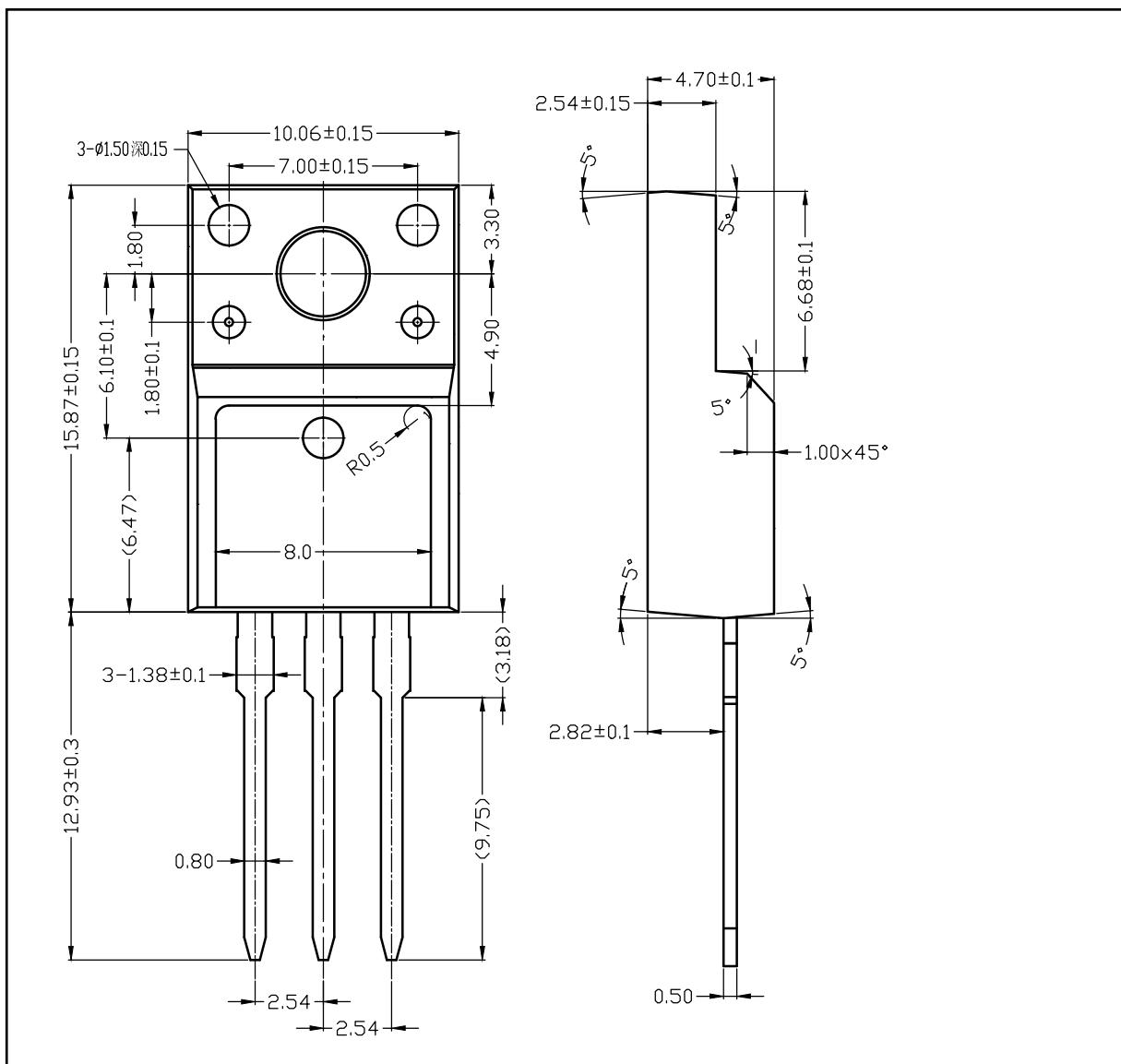
■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS(Cont.)



■ TO-220F-3L PACKAGE OUTLINE DIMENSIONS



■ TO-220-3L PACKAGE OUTLINE DIMENSIONS

